

37 CFR 1.501
 INFORMATION DISCLOSURE STATEMENT
 IN A PATENT
 (use several sheets if necessary)



Docket No.
 113278-005

Serial No.
 10/062,687

Applicant:
 Okuyama et al..

Filing Date
 Jan. 30, 2002

Group Art Unit

U.S. PATENT DOCUMENTS

Examiner's Initials		Document Number	Date	Name	Class	Subclasses	Filing Date If appropriate
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclasses	Translation	
							Yes	No
<i>JMS</i>	AL	6-45648	2-18-94	Japan				
<i>JMS</i>	AM	9-129974	5-16-97	Japan				
<i>JMS</i>	AN	11-26883	1-29-99	Japan				
	AO							
	AP							
	AQ							
	AR							
	AS							

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>JMS</i>	AT	Applied Physics Letters, Vol. 76, Number 22, 29 May 2000, "Selective growth at InGaN quantum dot structures and their microphotoluminescence at room temperature, Tachibani et al., pages 3212-3214
<i>JMS</i>		Journal of Crystal Growth 189/190 (1998) 83-86, "Spatial control of InGaN luminescence by MOCVD selective epitaxy", Kaplnek et al.
<i>JMS</i>		Journal of Crystal Growth, Volume 204, No. 3, pp. 247-418 July 11 (1999), Stringfellow, et al.

Examiner

Date Considered

1/15/04

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

#3

INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION (Use several sheets if necessary) PTO Form 1449	Atty Docket No. 113278-005	Application No. 10/062,687
	Applicant Hiroyuki Okuyama, et al.	
	Filing Date 1/30/02	Group Unknown

US PATENT DOCUMENTS

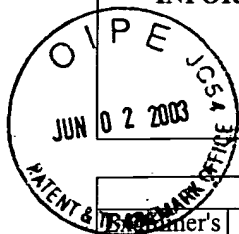
Examiner's Initials	Document Number	Publication Date	Inventor	Class	Subclass	Filing Date If Appropriate
JMB	5,981,977	11/09/99	Furukawa et al.			

FOREIGN PATENT DOCUMENTS

Examiner's Initials	Document Number	Publication Date	Country	Class	Subclass	Translation	
						Yes	No
JMB	08-255929	10/01/96	Japan				
JMB	09-199419	07/31/97	Japan				
JMB	10-265297	10/06/98	Japan				
JMB	10-270801	10/09/98	Japan				
JMB	10-312971	11/24/98	Japan				
JMB	10-321910	12/04/98	Japan				
JMB	11-238687	08/31/99	Japan				
JMB	11-274568	10/08/99	Japan				
JMB	2000-012976	01/14/00	Japan				
JMB	2000-150391	05/30/00	Japan				

Examiner's Initials	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)
JMB	J. Wang et al., Fabrication of nanoscale structures of InGaN by MOCVD lateral overgrowth, Journal of Crystal Growth 197 (1999), pp. 48-53.
JMB	Raj Singh et al., <i>Selective Area Growth of GaN Directly on (0001) Sapphire by the HVPE Technique</i> , MRS Internet Journal Nitride Semiconductor Research, 3, 13 (1998), pp. 1-4.
JMB	Zhigang Mao, et al., <i>Defects in GaN Pyramids Grown on Si(111) Substrates by Selective Lateral Overgrowth</i> , pp. 1-6; Materials Research Society Meeting in Boston, Mass. (1998).

Examiner: <i>[Signature]</i>	Date Considered: 1/15/04
*Examiner: Initial if citation considered, whether or not citation is in conformance with PEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	



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INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary) PTO Form 1449	Atty Docket No. 112857-382	Application No. 10/062,687
	Applicant Okuyama, et al.	
	Filing Date January 30, 2002	Group 2811

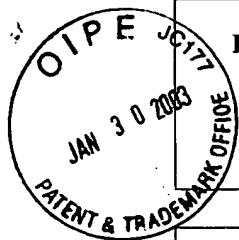
U.S. PATENT DOCUMENTS						
Examiner's Initials	Document Number	Publication Date	Inventor	Class	Subclass	Filing Date If Appropriate

FOREIGN PATENT DOCUMENTS							
Examiner's Initials	Document Number	Publication Date	Country	Class	Subclass	Translation	
						Yes	No
<i>QMS</i>	63-188938	08-04-88	Japan				
<i>QMS</i>	08-008217	01-12-96	Japan				
<i>QMS</i>	10-270801	10-09-98	Japan				
<i>QMS</i>	10-312971	11-24-98	Japan				
<i>QMS</i>	11-251253	09-17-99	Japan				
<i>QMS</i>	11-312840	11-09-99	Japan				
<i>QMS</i>	2000-068593	03-03-00	Japan				
<i>QMS</i>	2000-183451	06-30-00	Japan				
<i>QMS</i>	2000-223417	08-11-00	Japan				
<i>QMS</i>	2001-085738	03-30-01	Japan				
<i>QMS</i>	2001-217503	08-10-01	Japan				
<i>QMS</i>	2002-185660	12-12-02	Japan				

Examiner's Initials	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)
<i>QMS</i>	Zheleva et al., <i>Pendeo-epitaxy – a new approach for lateral growth of gallium nitride structures</i> , MRS Internet J. Nitride Semicond. Res. 4S1, G3.38 (1999).
<i>QMS</i>	Kapolnek et al., <i>Spatial control of InGaN luminescence by MOCVD selective epitaxy</i> , Journal of Crystal Growth, 189/190 (1998) pp. 83-86.

Examiner: <i>[Signature]</i>	Date Considered: <i>1/15/04</i>
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**INFORMATION DISCLOSURE CITATION
IN AN APPLICATION**
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PTO Form 1449

Atty Docket No. 112857-382	Application No. 10/062,687
Applicant Okuyama et al.	
Filing Date January 30, 2002	Group Unknown

U.S. PATENT DOCUMENTS

Examiner's Initials	Document Number	Publication Date	Inventor	Class	Subclass	Filing Date If Appropriate
<i>AM</i>	5,177,405	01-05-93	Kusuda et al.			
<i>AM</i>	5,981,977	11-09-99	Furukawa et al.			

FOREIGN PATENT DOCUMENTS

Examiner's Initials	Document Number	Publication Date	Country	Class	Subclass	Translation	
						Yes	No
<i>AM</i>	56-92577 ✓	07-27-81	Japan				
<i>AM</i>	57-45583 ✓	03-15-82	Japan				
<i>AM</i>	57-52071 ✓	03-27-82	Japan				
<i>AM</i>	57-52072 ✓	03-27-82	Japan				
<i>AM</i>	57-52073 ✓	03-27-82	Japan				
<i>AM</i>	58-50577 ✓	03-25-83	Japan				
<i>AM</i>	61-156780 ✓	07-16-86	Japan				
<i>AM</i>	2-263668 ✓	10-26-90	Japan				
<i>AM</i>	03-035568	02-15-91	Japan				
<i>AM</i>	06-067044 ✓	03-11-94	Japan				
<i>AM</i>	6-45648 ✓	02-18-94	Japan				
<i>AM</i>	07-199829 ✓	04-08-95	Japan				
<i>AM</i>	9-129974 ✓	05-16-97	Japan				
<i>AM</i>	WO 97/44612 ✓	11-27-97	PCT				
<i>AM</i>	11-26883 ✓	01-29-99	Japan				
<i>AM</i>	11-075019 ✓	03-16-99	Japan				
<i>AM</i>	11-177138 ✓	07-02-99	Japan				
<i>AM</i>	11-514136 ✓	11-30-99	Japan				
<i>AM</i>	11-346004 ✓	12-14-99	Japan				

Examiner:

Ameyama

Date Considered:

1/15/04

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